

# **CMOS RF Power Amplifiers: Nonlinear, Linear, Linearized**

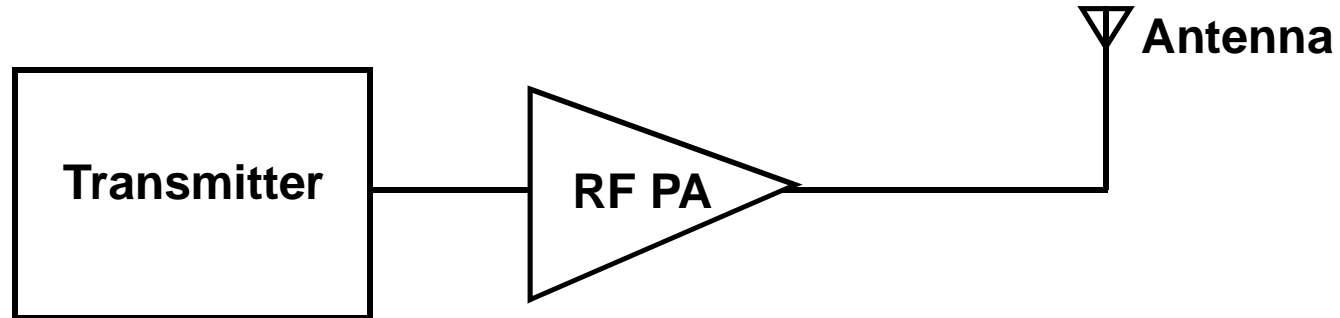
**David Su**

**Atheros Communications  
Sunnyvale, California**

# Outline

- **Introduction**
- **Nonlinear Power Amplification**
- **Linear Power Amplification**
- **Linearization using Envelope Elimination and Restoration**
- **Conclusion**

# RF Power Amplification

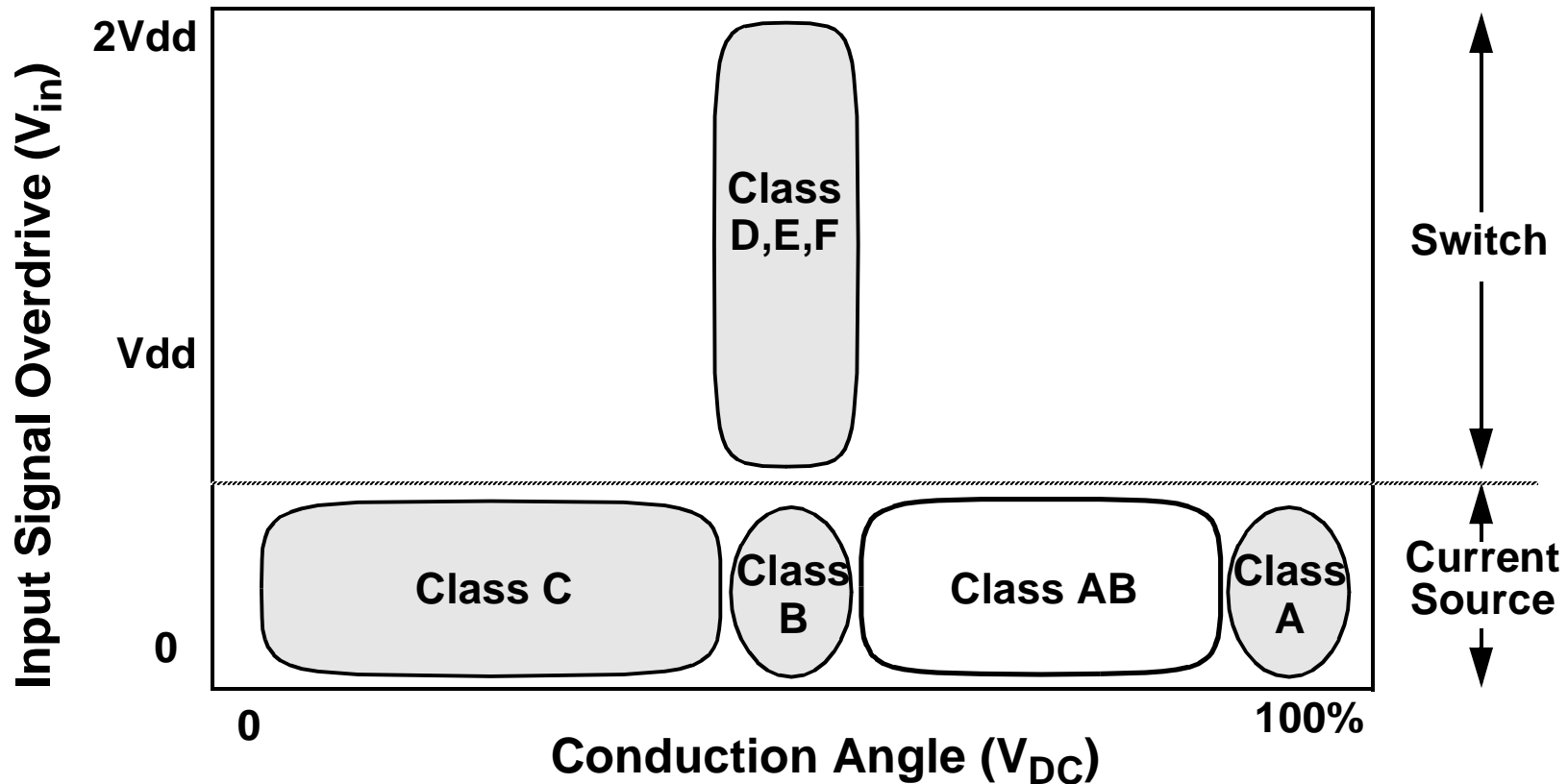


- **Purpose:** Delivers “narrow-band” RF power to a 50-ohm antenna
- **Performance:** Output Power  
Efficiency  
Linearity

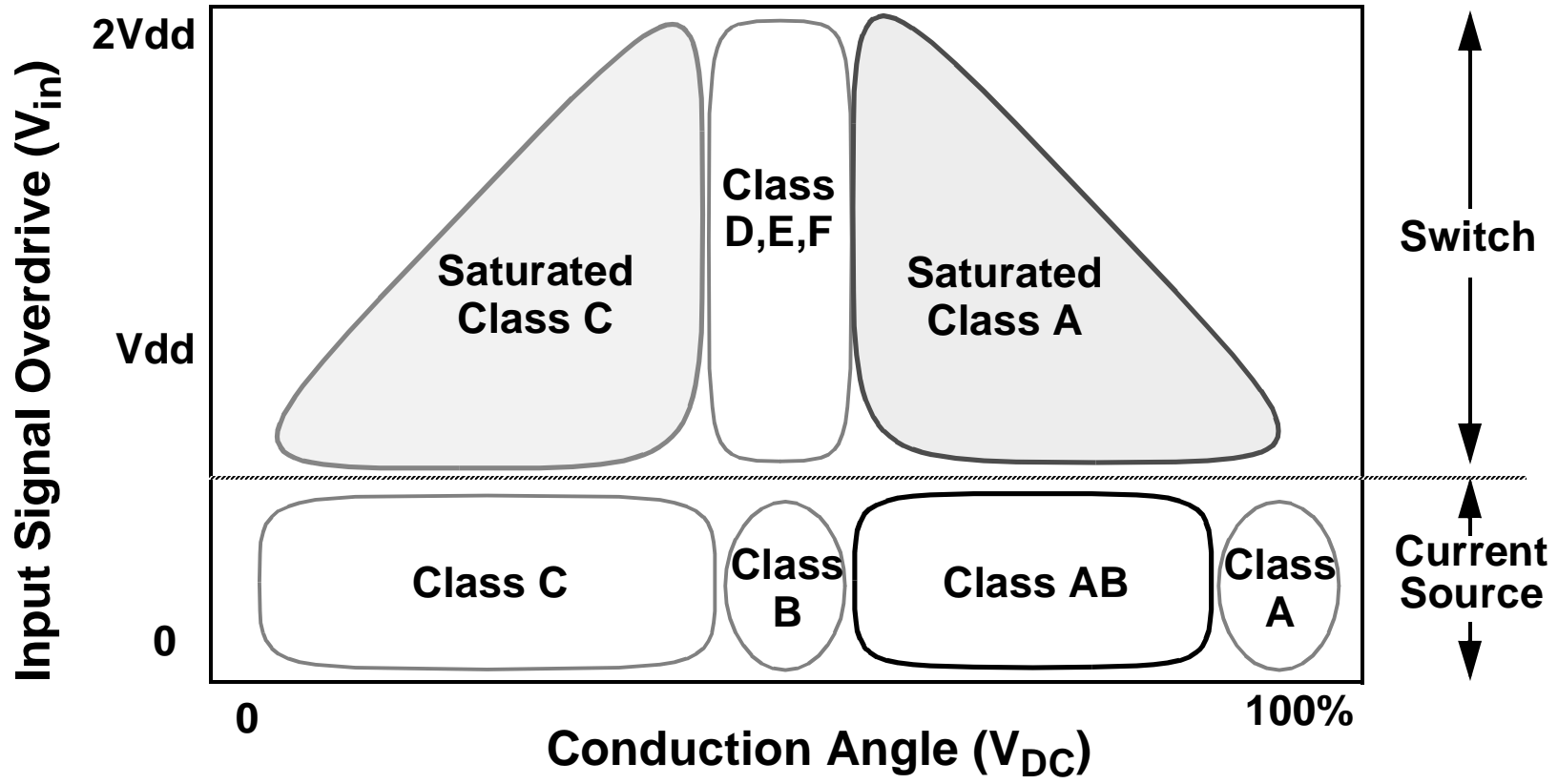
# Traditional PA Classification

Class	Modes	Conduction Angle	Output Power	Maximum Efficiency	Gain	Linearity
A	Current Source	100%	moderate	50%	Large	Good
B		50%	moderate	78.5%	Moderate	Moderate
C		< 50%	small	100%	Small	Poor
D	Switch	50%	large	100%	Small	Poor
E		50%	large	100%	Small	Poor
F		50%	large	100%	Small	Poor

# PA Classification & Input Drive



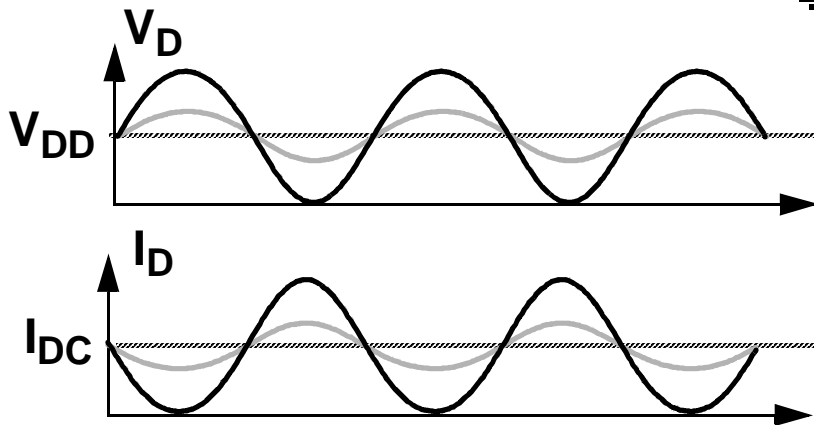
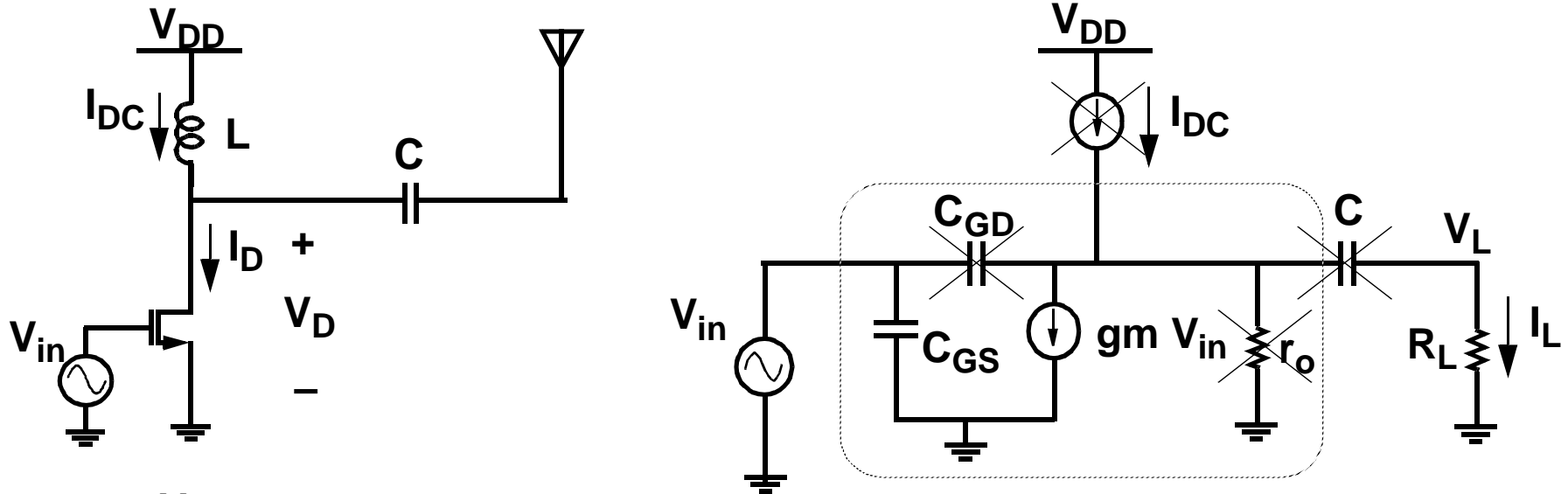
# Power Amplifier Classification



# CMOS for RF Power Amplification

- **Traditional RF PAs use GaAs / Bipolar.**
- **Advantages of CMOS:**
  - Low cost, high-yield, high-integration
  - Efficient switched-mode amplifier
- **Disadvantages of CMOS:**
  - Low bandwidth
  - Low breakdown voltage

# Simplified RF Output Stage

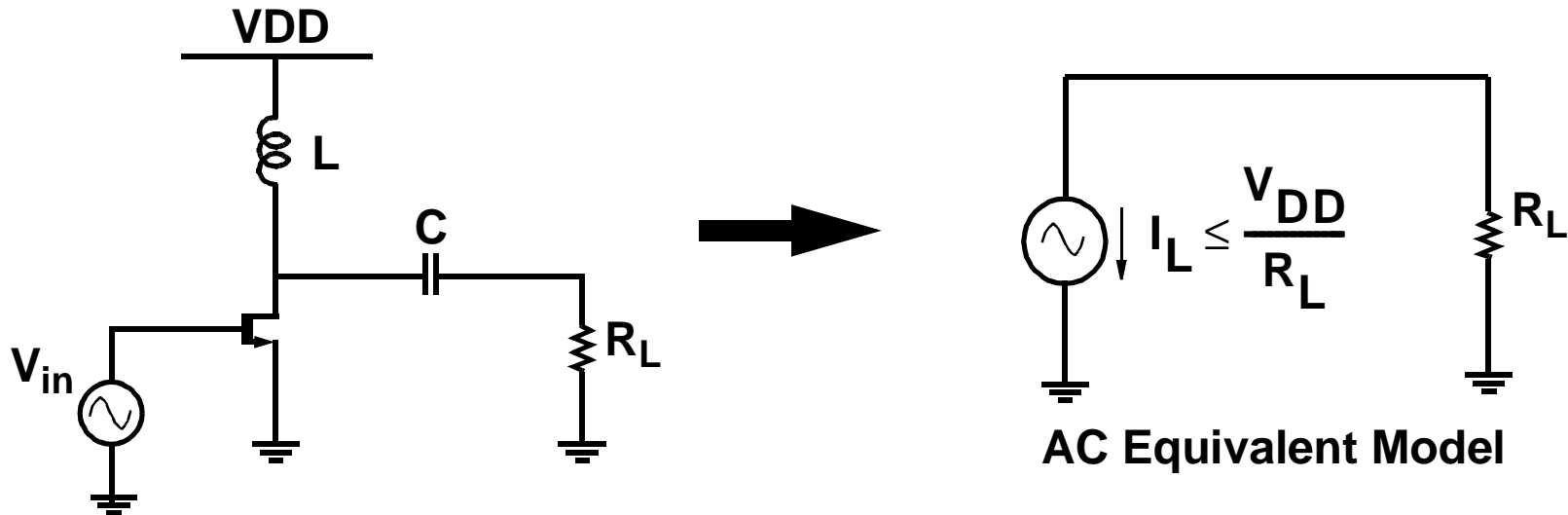


$$I_D = g_m V_{in}$$

$$I_L \leq \frac{V_{DD}}{R_L}$$



# Class-A (Linear) Operation

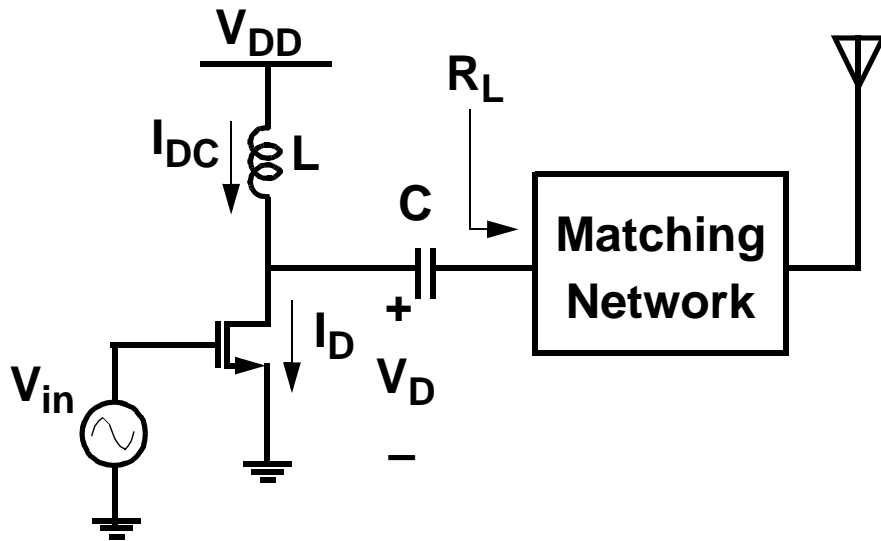


$$P_{out} = \frac{1}{2} I_L^2 R_L \leq \frac{V_{DD}^2}{2R_L}$$

For  $P_{out} = 1 \text{ W}$  (Class A),  $R_L = 4.5 \Omega$  @  $V_{DD} = 3\text{V}$   
 $R_L = 3.1 \Omega$  @  $V_{DD} = 2.5\text{V}$

⇒ Needs Impedance Transformation Network →  $50 \Omega$  antenna  
 ⇒ Keep parasitic loss  $\ll R_L$  of  $3.1 \Omega$

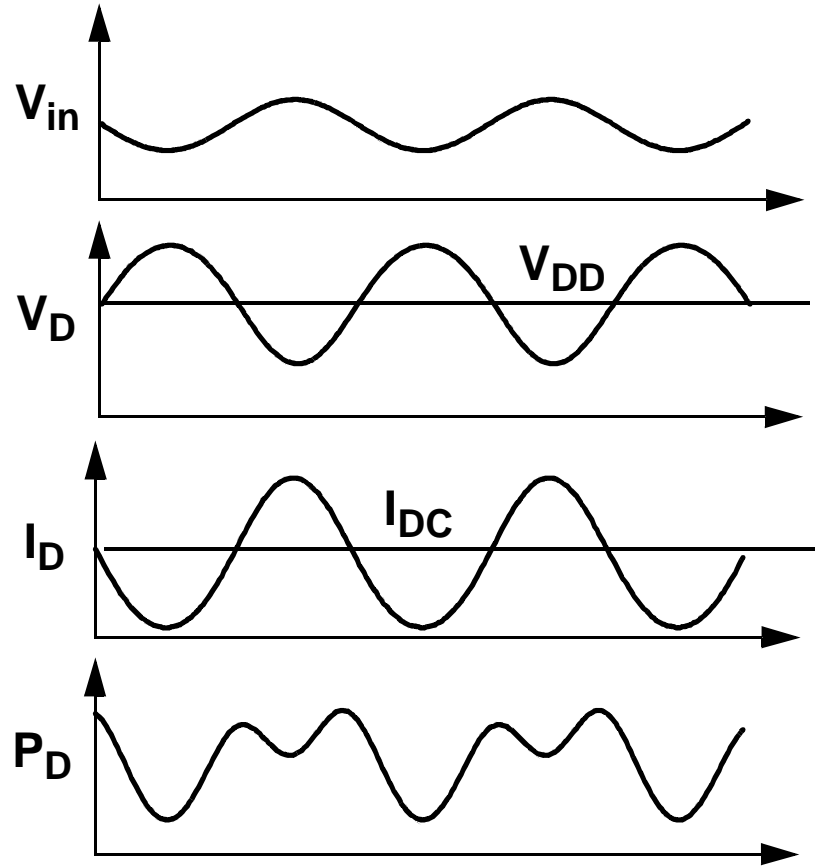
# Efficiency of Class A operation



$$P_{out} \leq \frac{V_{DD}^2}{2R_L}$$

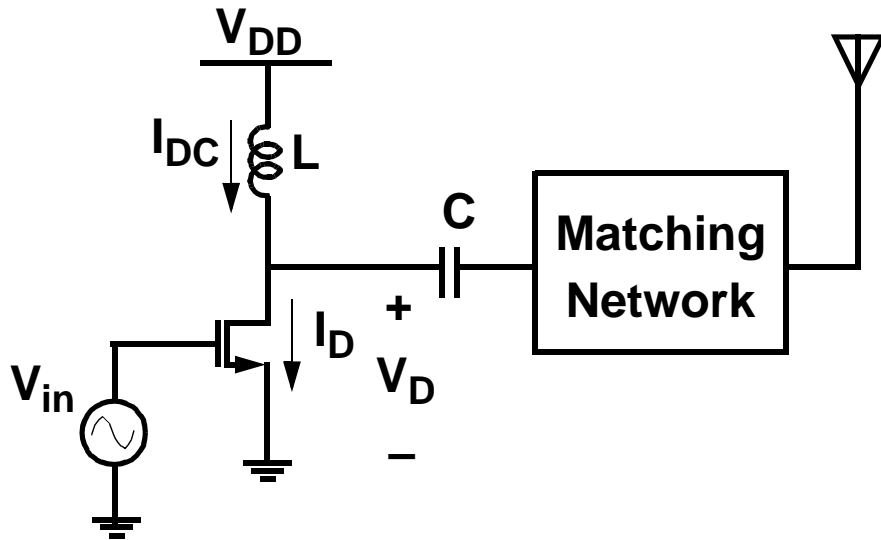
$$P_{supply} = I_{DC} \times V_{DD} = \frac{V_{DD}^2}{R_L}$$

$$\text{Efficiency} = \frac{P_{out}}{P_{supply}} \leq 50\%$$



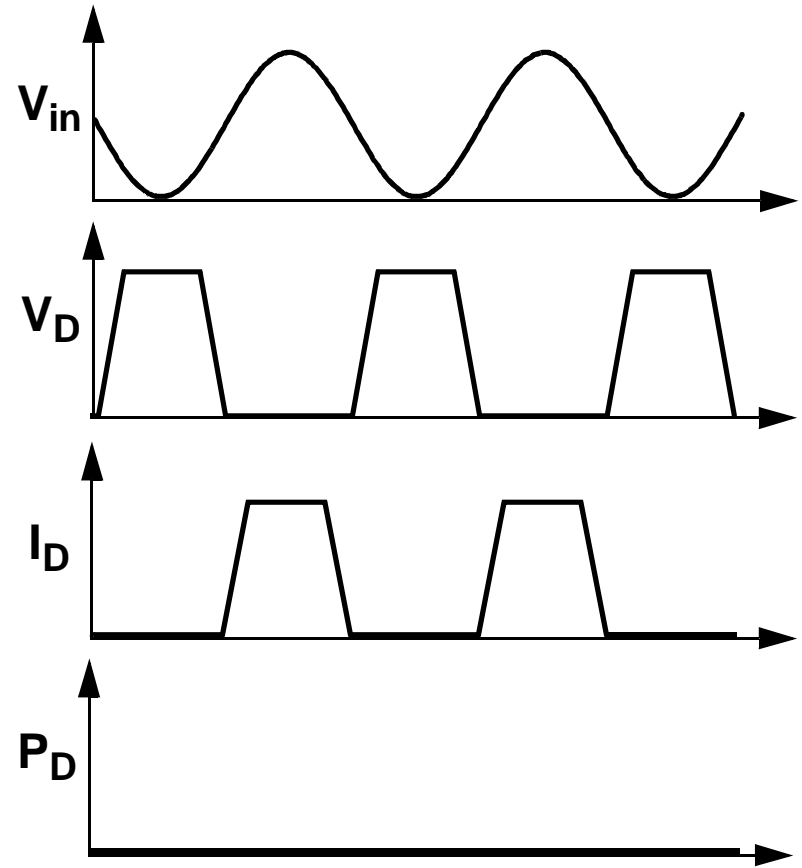
$$P_D = I_D \times V_D \downarrow \Rightarrow \text{Efficiency} \uparrow$$

# Efficiency-Linearity Tradeoff



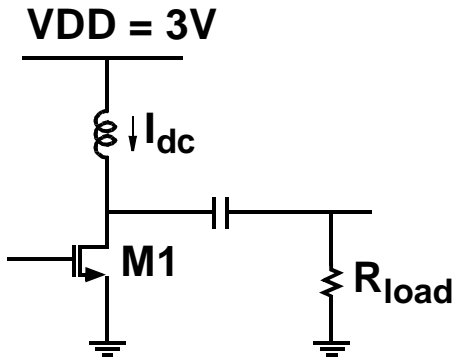
- Large input signal
- Square wave output  $I_D$  and  $V_D$
- Non-overlapping  $I_D$  and  $V_D$

$$P_{out} = \frac{V_{DD}^2}{R_L}$$



$P_D = 0 \Rightarrow \text{Efficiency} = 100\%$

# Low-Voltage Operation



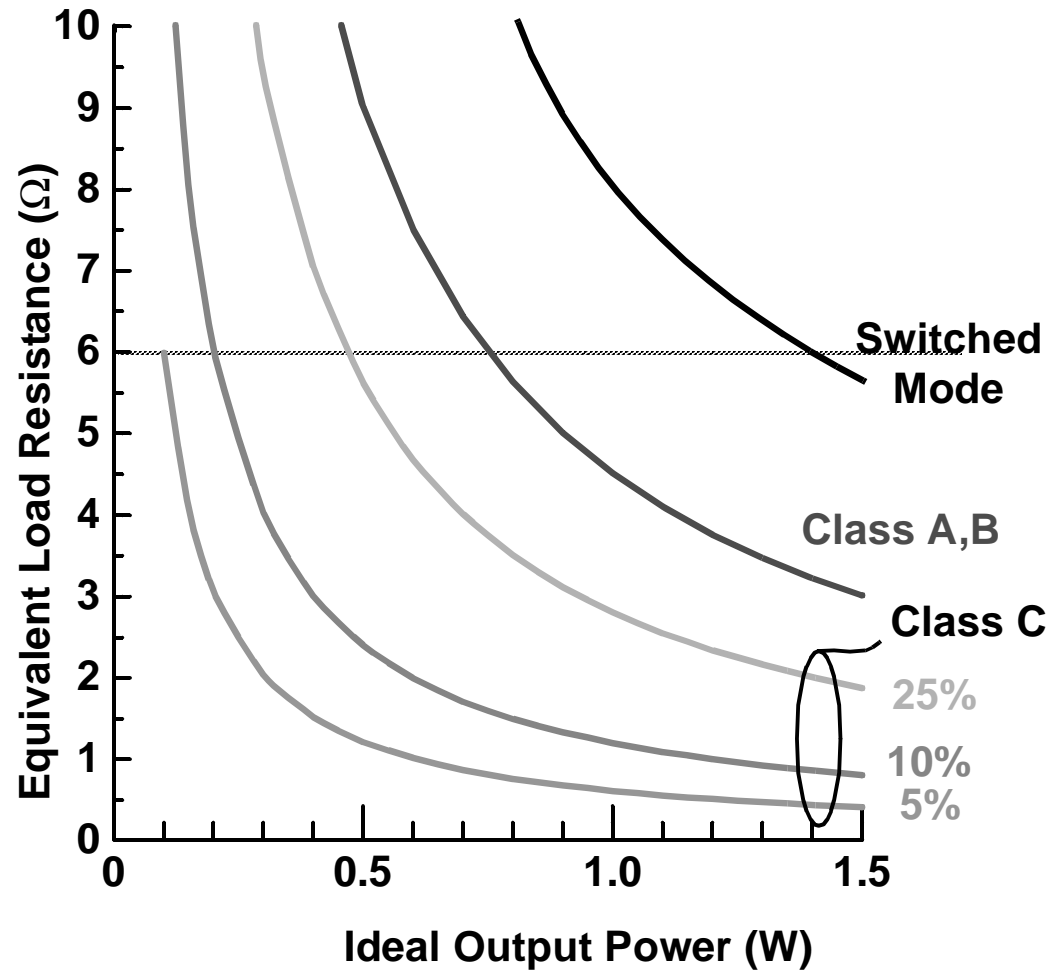
$$P_{out} \approx \frac{VDD^2}{nR_{load}}$$

$$R_{load} \approx \frac{VDD^2}{nP_{out}}$$

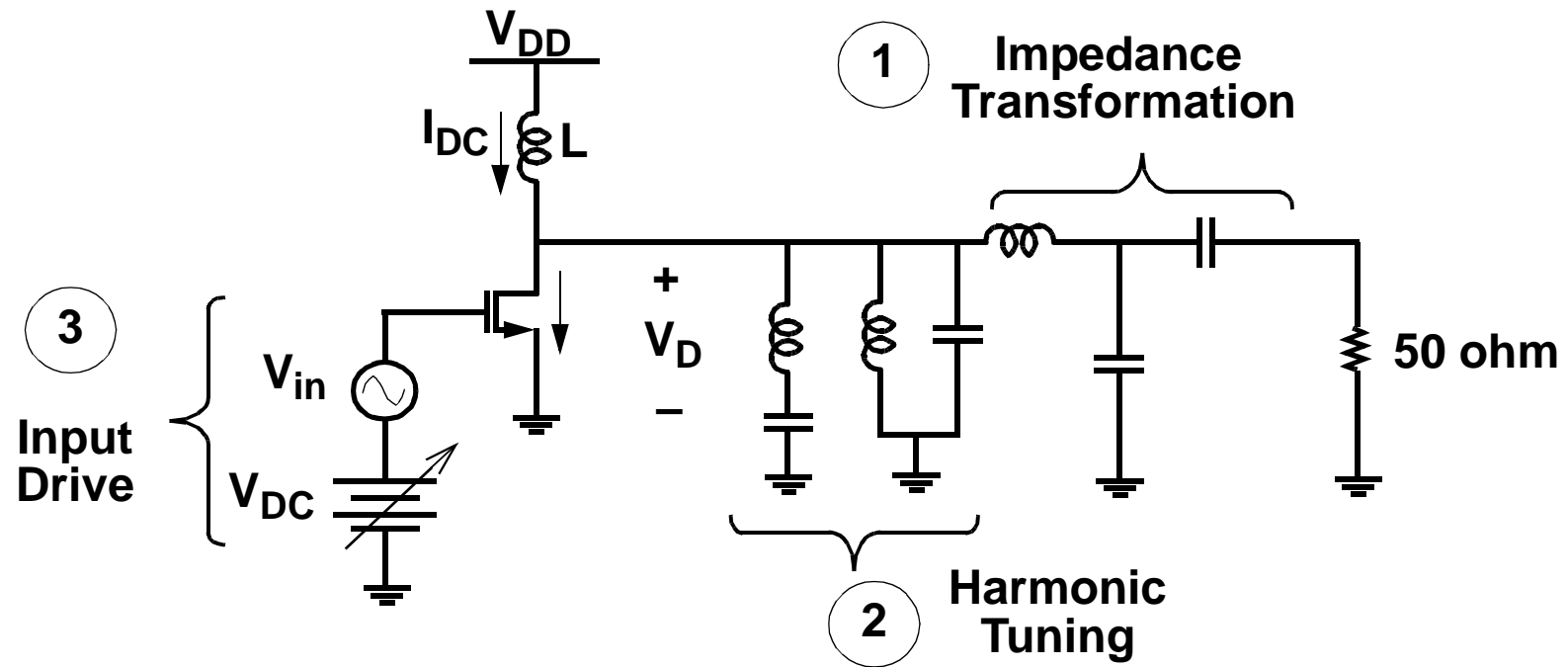
Switched-Mode:  $n = 1$

Class A,B:  $n = 2$

Class C:  $n > 2$



# Practical Power Amplifier Design



## LOAD PULL Optimization

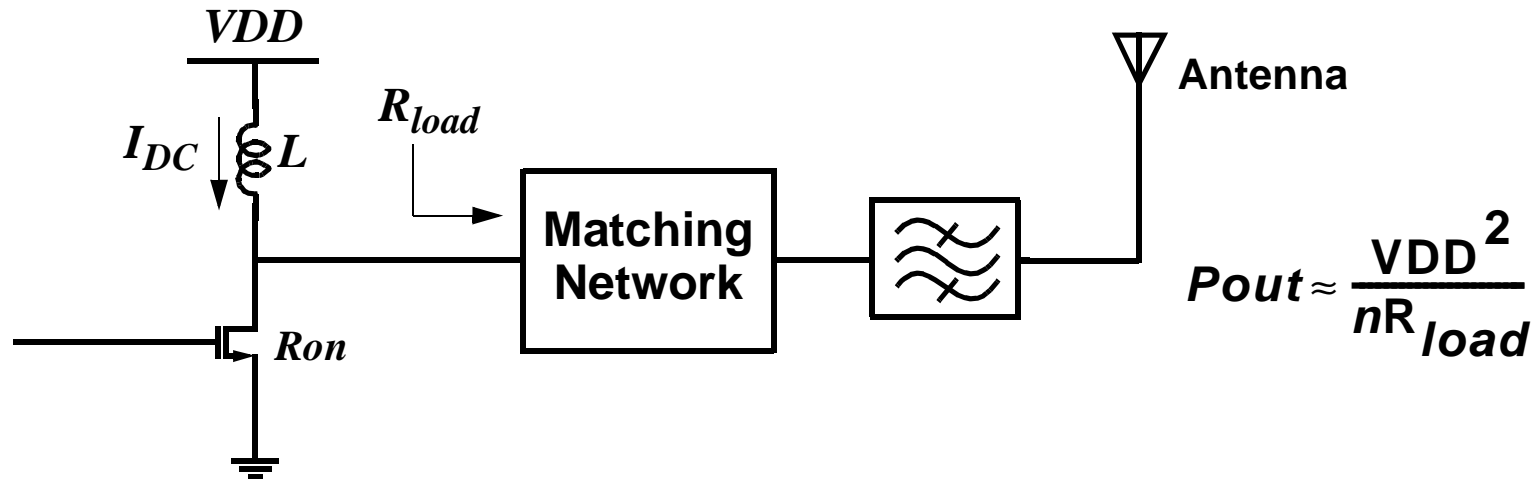
1. Impedance transformation: Output Power
2. Harmonic Tuning: short @  $2f_c$  & open @  $3f_c$  for non-overlap  $I_D$  &  $V_D$  to maximize efficiency
3. Input drive:  $V_{DC}$  -> Conduction Angle;  $V_{in}$  -> current source vs switch

# Nonlinear Power Amplifier

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- **Hewlett Packard Labs  
(with W. McFarland)**
- **800-MHz 32dBm AMPS PA with 42 %  
PAE in 0.8  $\mu\text{m}$  CMOS**

# Switched-Mode Design



Choose  $n = 1.5$  (assume 67% efficiency due to  $R_{on} > 0$ ),

$VDD = 2.5V$ ,

For  $P_{out} = 1 W$ ,

$$R_{load} = 4.2 \Omega$$

$$I_{DC} = 0.49A$$

$$R_{on} = 1 \Omega$$

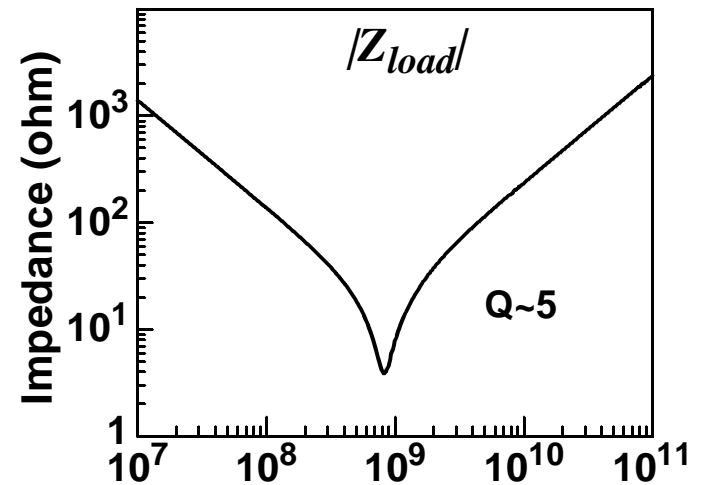
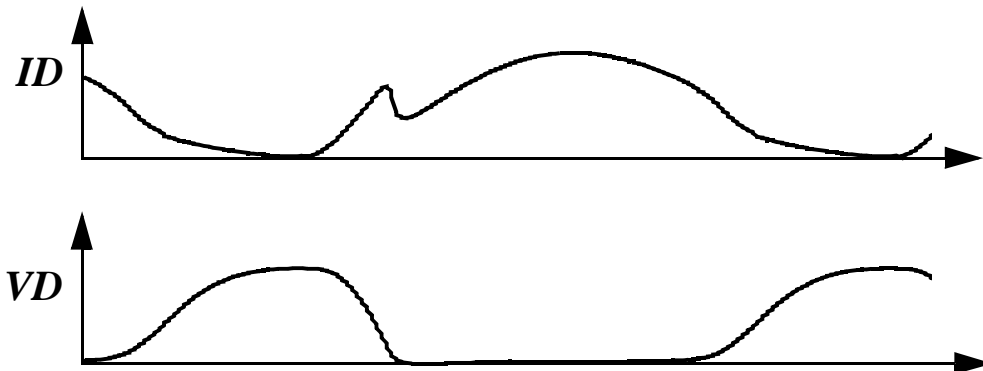
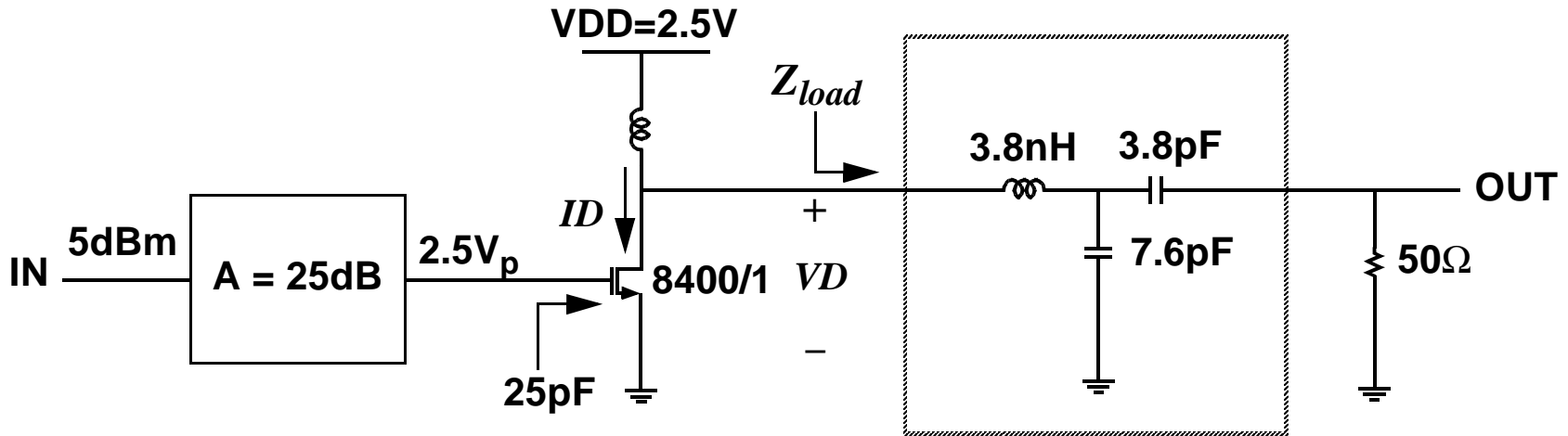
$$[P_{out} = VDD^2/n R_{load}]$$

$$[I_L \text{ (peak)} = I_{DC} \ \& \ P_{out} = 0.5 \times I_{DC}^2 \times R_{load}]$$

$$[\text{Assume no overlap; } P_D = 0.5W = 0.5 \times (2 I_{DC})^2 \times R_{on}]$$

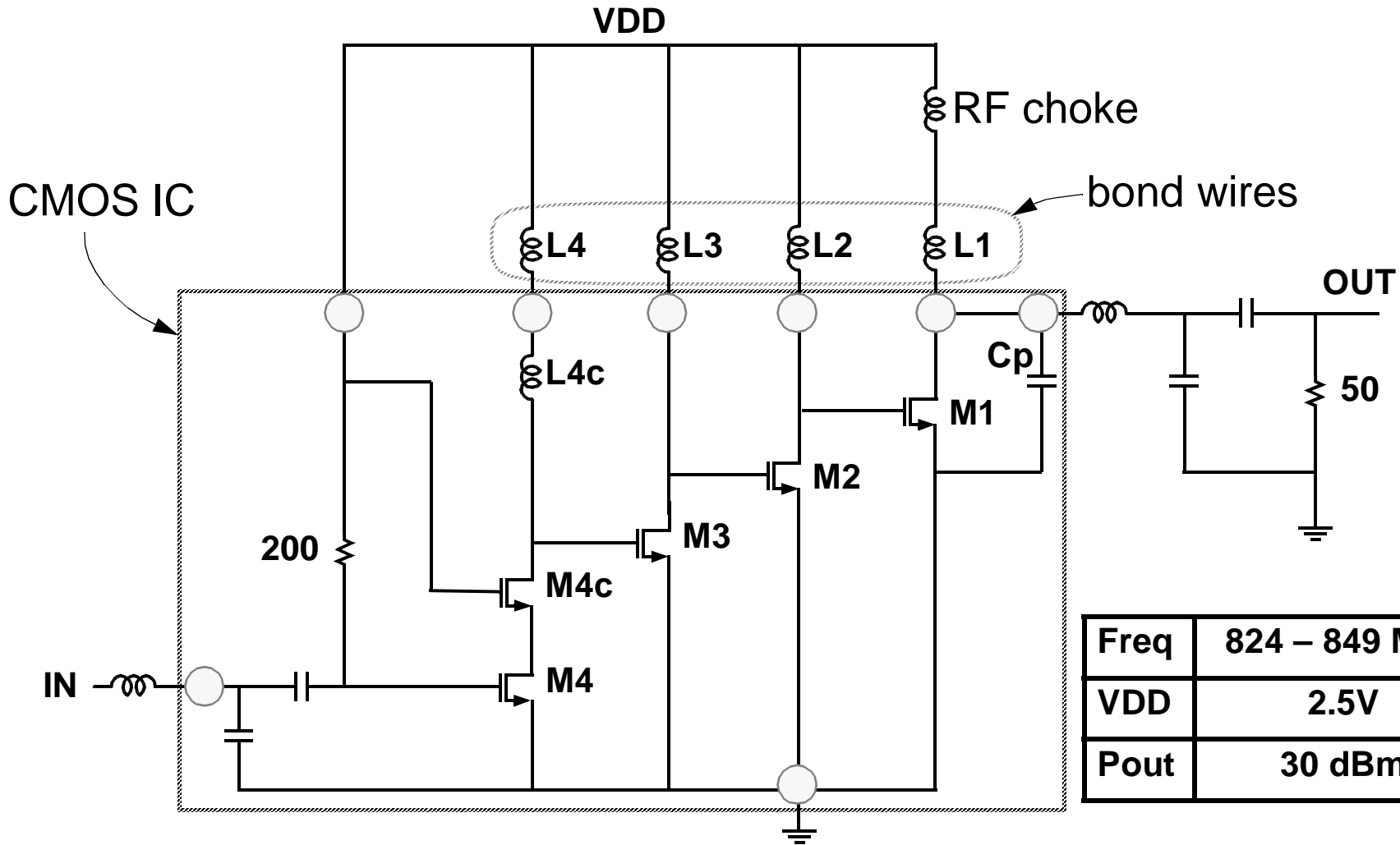
$\Rightarrow$  Output transistor sizing:  $R_{on} < 1 \Omega$

# Output Stage Design





# Complete Amplifier

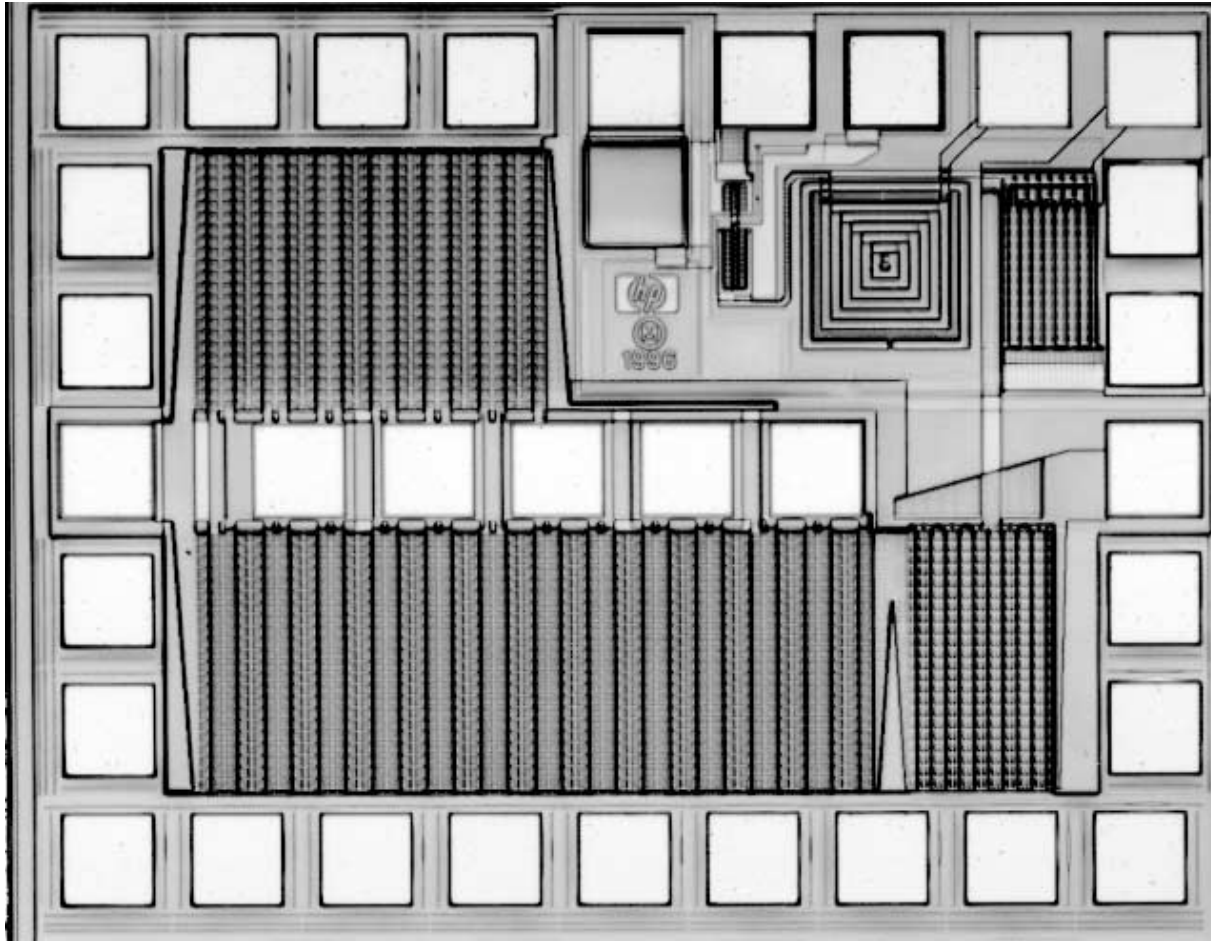


Freq	824 – 849 MHz
VDD	2.5V
Pout	30 dBm

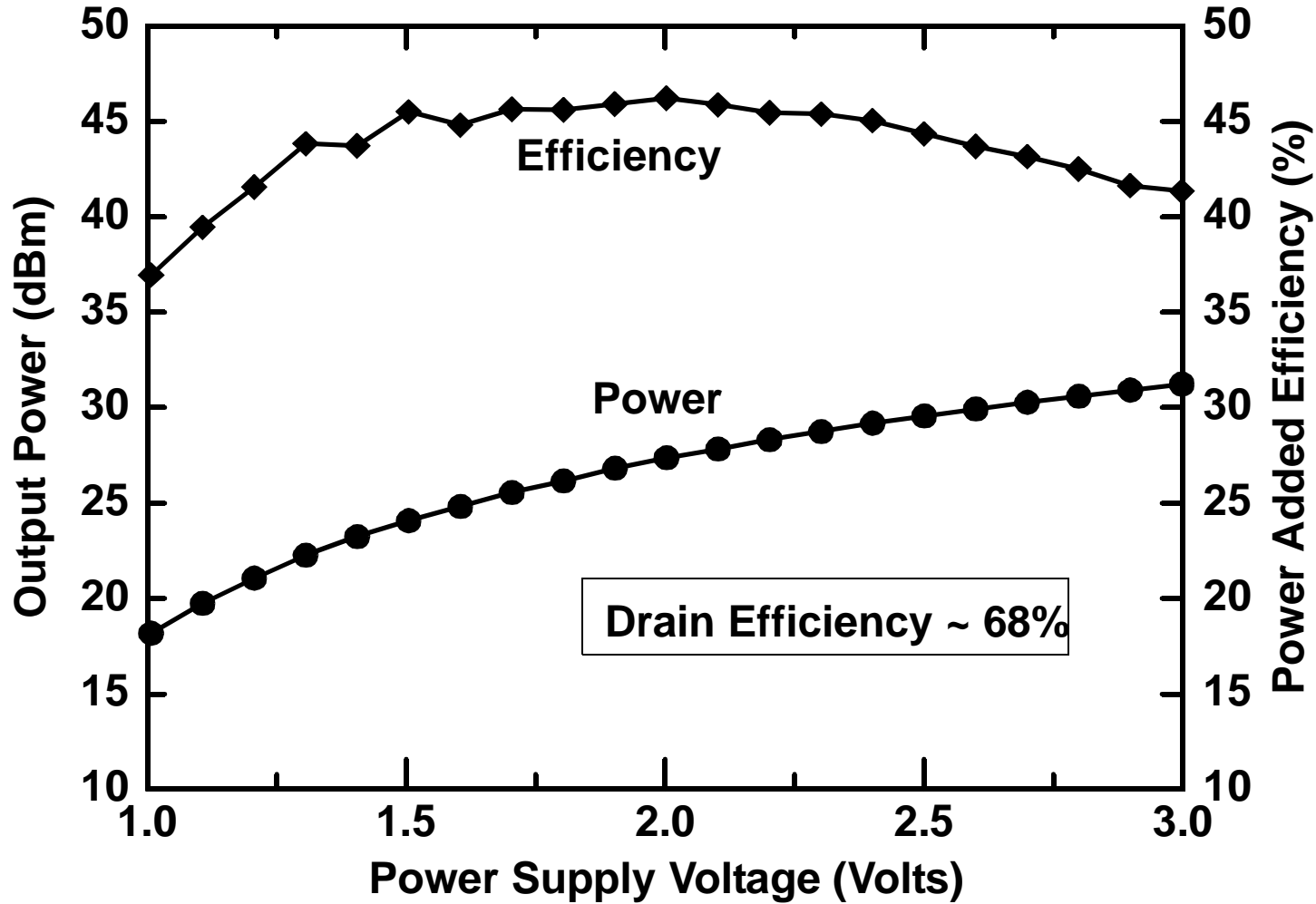
# Die Photo

0.8 $\mu\text{m}$  CMOS

1.5 mm<sup>2</sup>



# Measured $P_{OUT}$ and Efficiency



# Linear Power Amplifier

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- **Atheros Communications  
(with D. Weber et al)**
- **5-GHz 18dBm OFDM PA for IEEE  
802.11a in 0.25  $\mu\text{m}$  CMOS**

# Spectral-Efficient Modulation

- **64-QAM (Quadrature Amplitude Modulation)**
  - Large signal to noise ratio > 30dB
- **OFDM (Orthogonal Frequency Division Mux)**
  - Large peak to average power ratio of  $\sqrt{52}$  or 17dB

→ Requires High Linearity in PA

# Power Amplifier Design

- Large peak to average ratio (PAR) of  $\sqrt{52}$  or 17dB
- Signal peaks are infrequent: 0.25dB SNR degradation when PAR reduced to 6dB for 16-QAM\*.
- Implications:
  - Poor power efficiency
  - With 6dB PAR, to obtain 40mW (16dBm) requires  $P_{sat}$  of ~22dBm or 160mW
  - With 17dB PAR, to obtain 40mW (16dBm) requires  $P_{sat}$  of ~33dBm or 2W

\*Van Nee & Prasad, OFDM for Wireless Multimedia Communications, Artech House, 2000

# Linear PA makes efficient radios

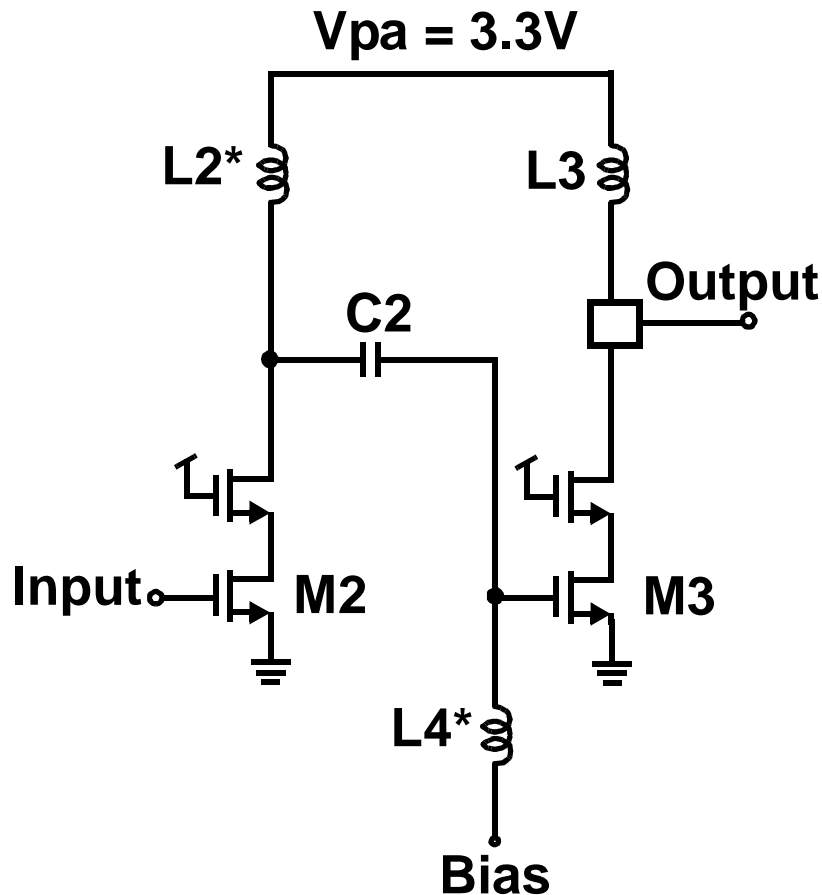
- **Frequency bandwidth is precious**  
**--> Maximize network capacity**
- **Energy/bit (battery life)**  
**More bits sent per second**  
**--> PA + the rest of the radio**  
**are ON for shorter duration**

# Linear PA Design

- **Input load impedance**
  - signal dependency
  - cascode
- **$V_{GS}$  overdrive**
  - dc bias with capacitive level-shift
- **Output load impedance**
  - impedance matching network
- **Stability**
  - cascode



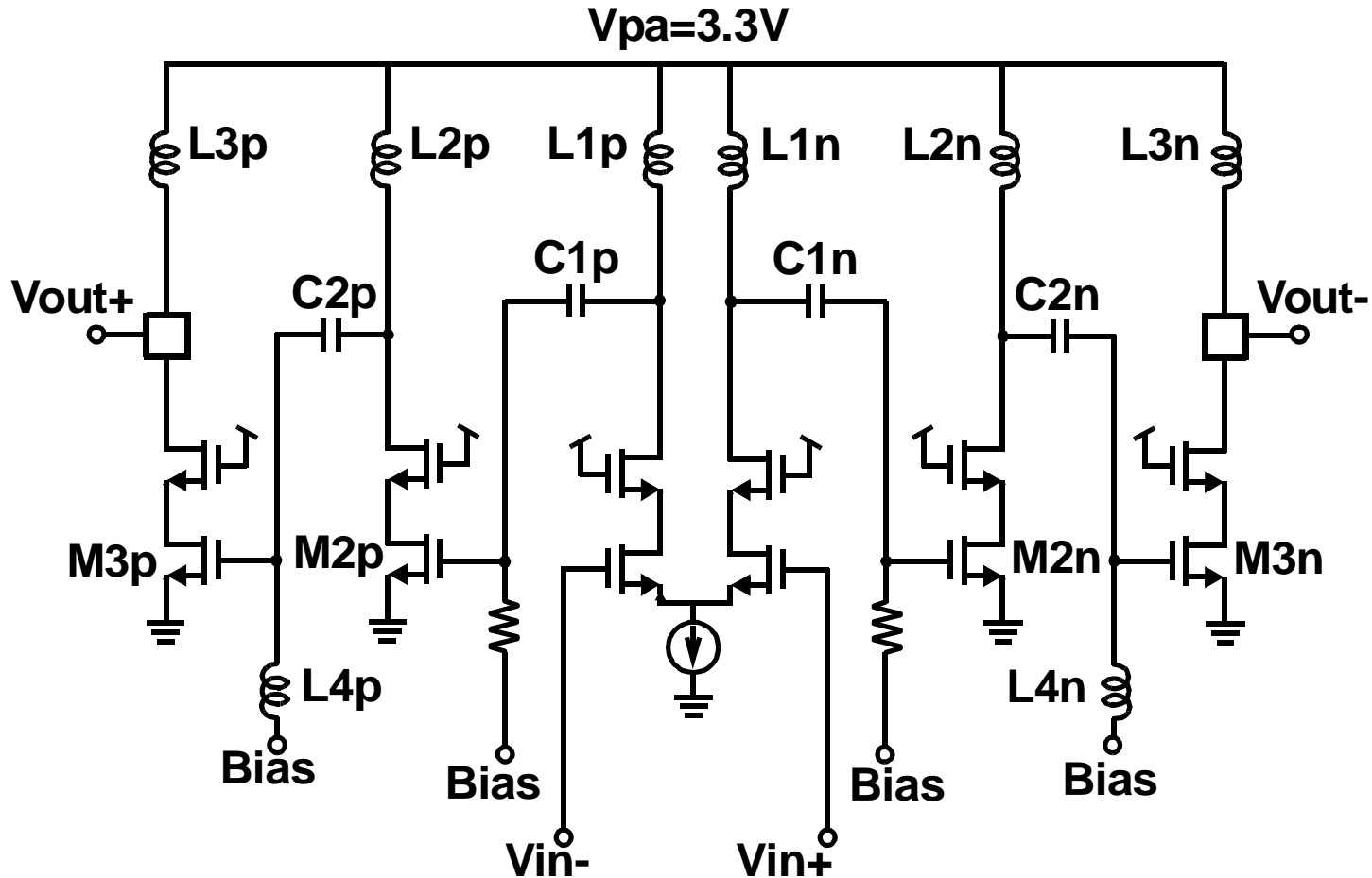
# Power Amplifier Topology



- Class A operation
- Cascoded
  - 3.3V supply voltage
  - Stability
- Capacitive Level-shift
  - Metal-2,3,4,5 stacks
- Inductive loads
- Differential
  - Off-chip balun

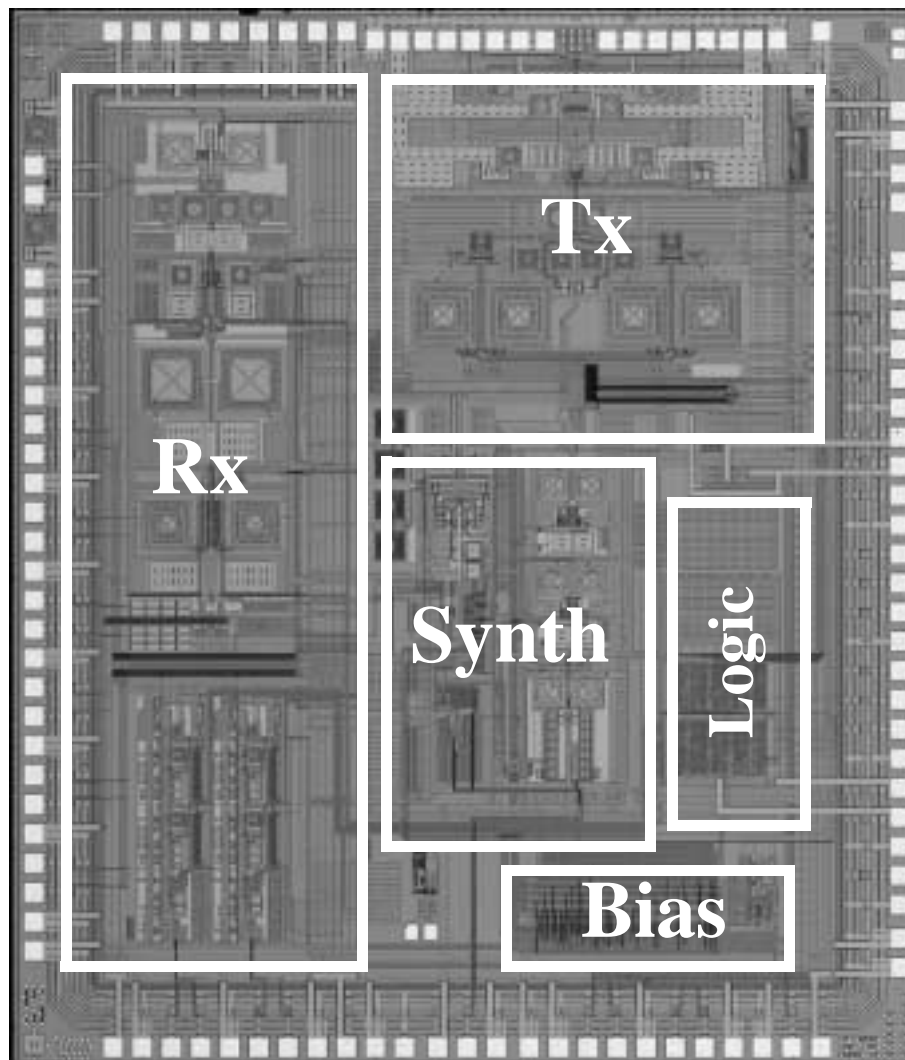
\* C.P. Yue and S.S. Wong, IEEE JSSC, May 1998

# Power Amplifier Schematic

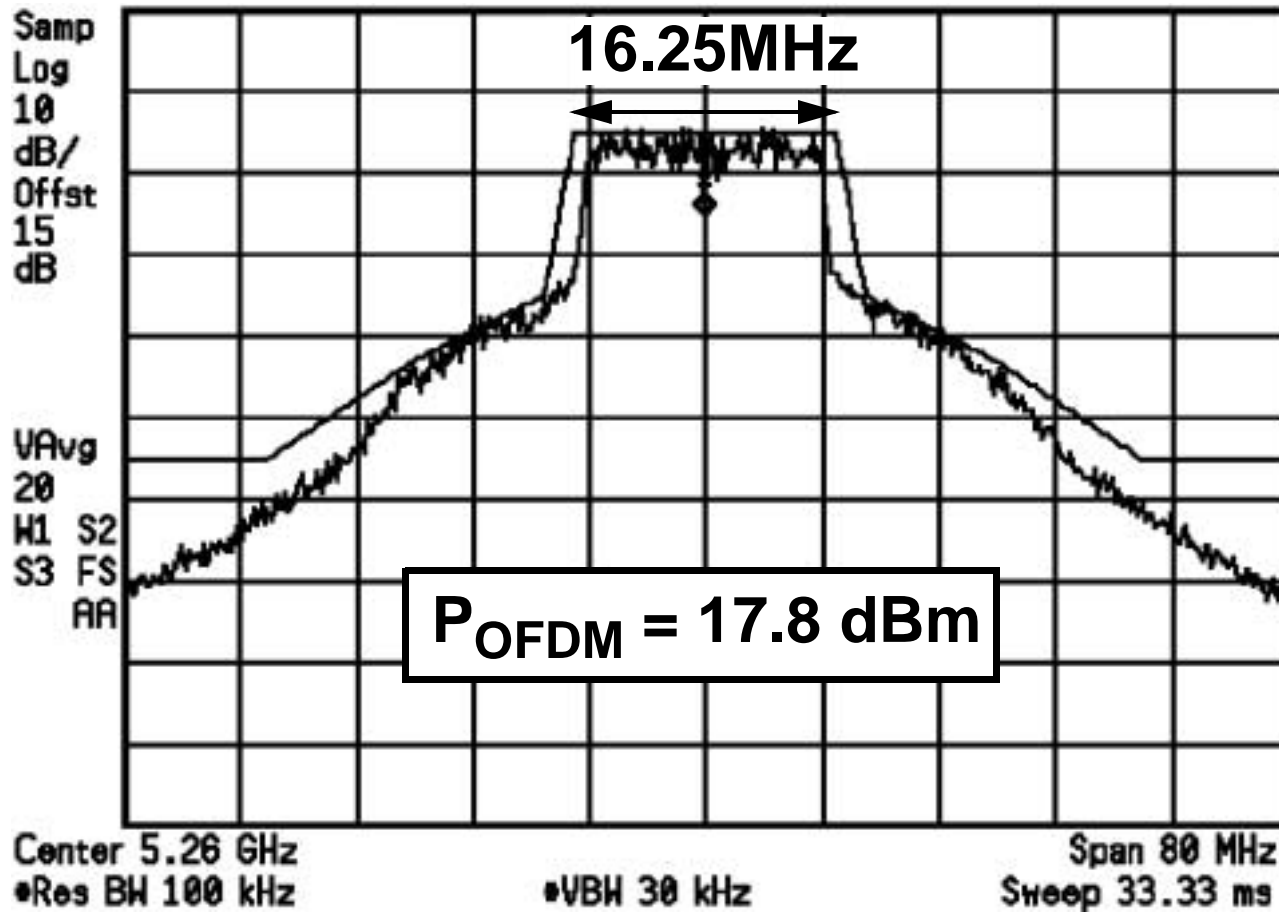


$P_{SAT} = 22 \text{ dBm}$

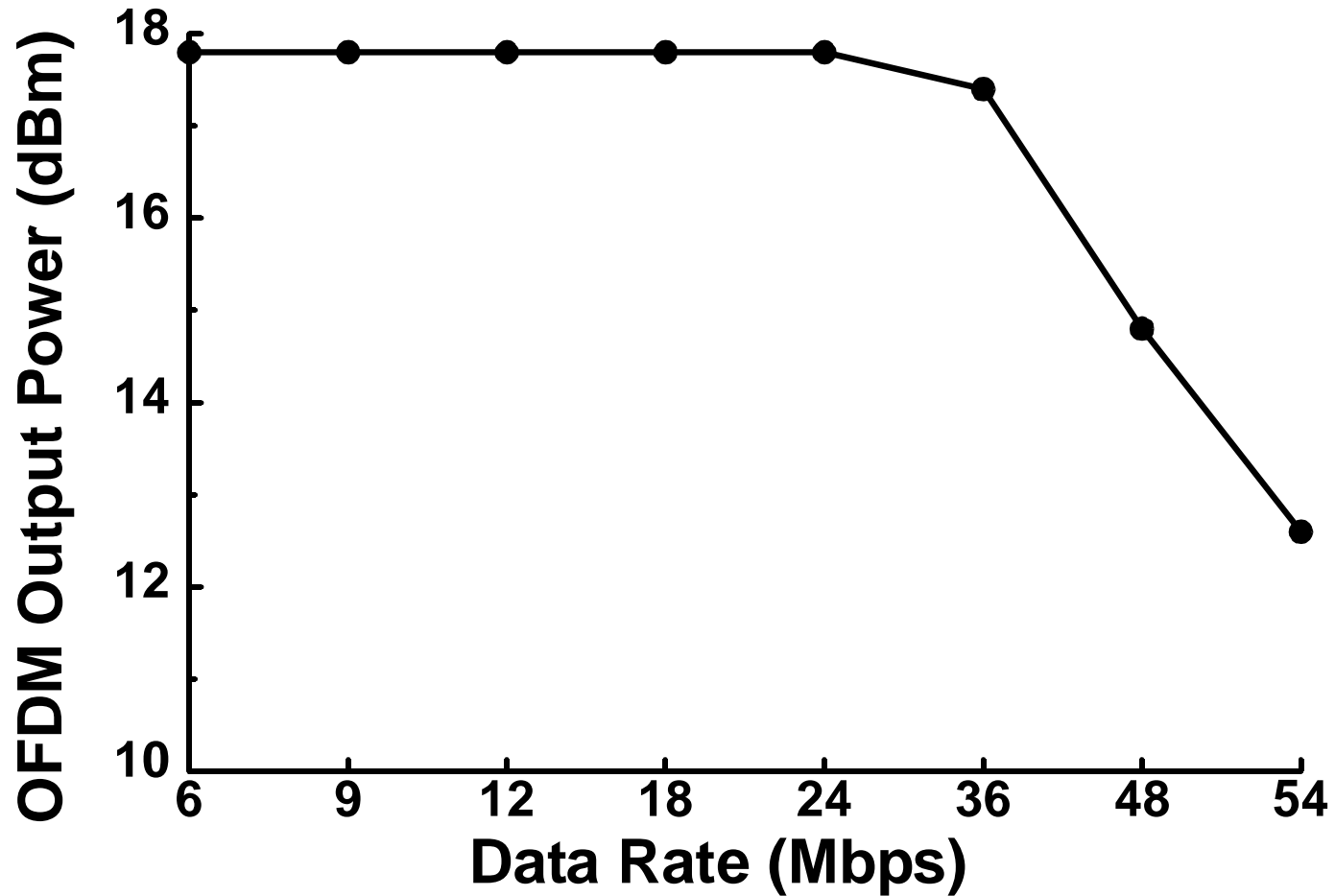
# Die Photograph



# Measured BPSK OFDM Spectrum



# Measured Transmit Output Power



# Linearized Power Amplification

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- **Hewlett Packard Labs  
(with W. McFarland)**
- **Linearization IC for NADC with  
efficiency improvement from 36% to  
49% using envelope elimination and  
restoration**

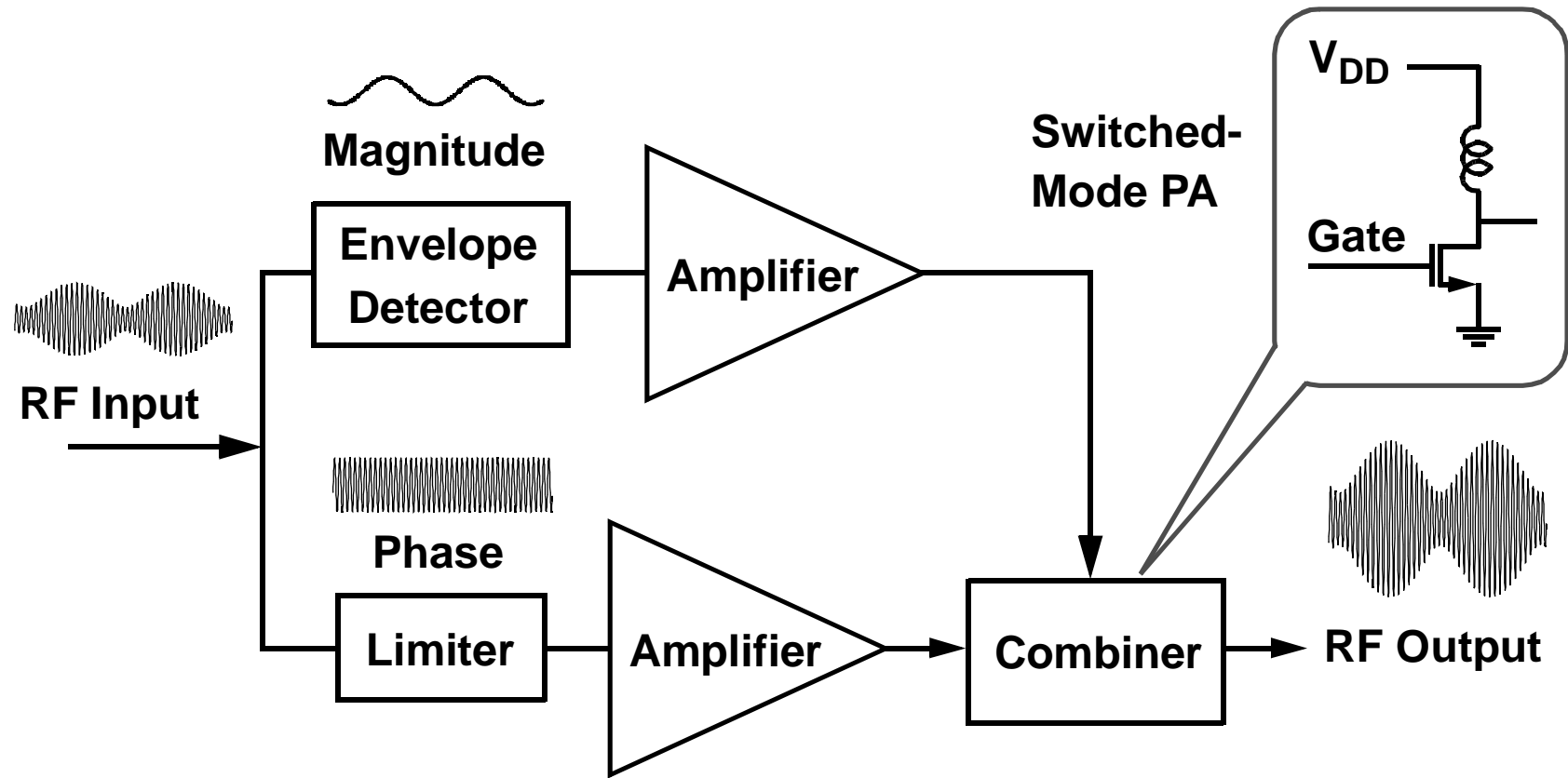
# Applying Integration to RF PA

## Transistors are *cheap*.

- **LARGE Output Power:** Use switched-mode output stage
- **HIGH Efficiency:** Use switched-mode output stage
- **GOOD Linearity:** Use linearization circuits so that the output stage does not need to be linear.

**SOLUTION: Switched-mode output stage  
+ linearization.**

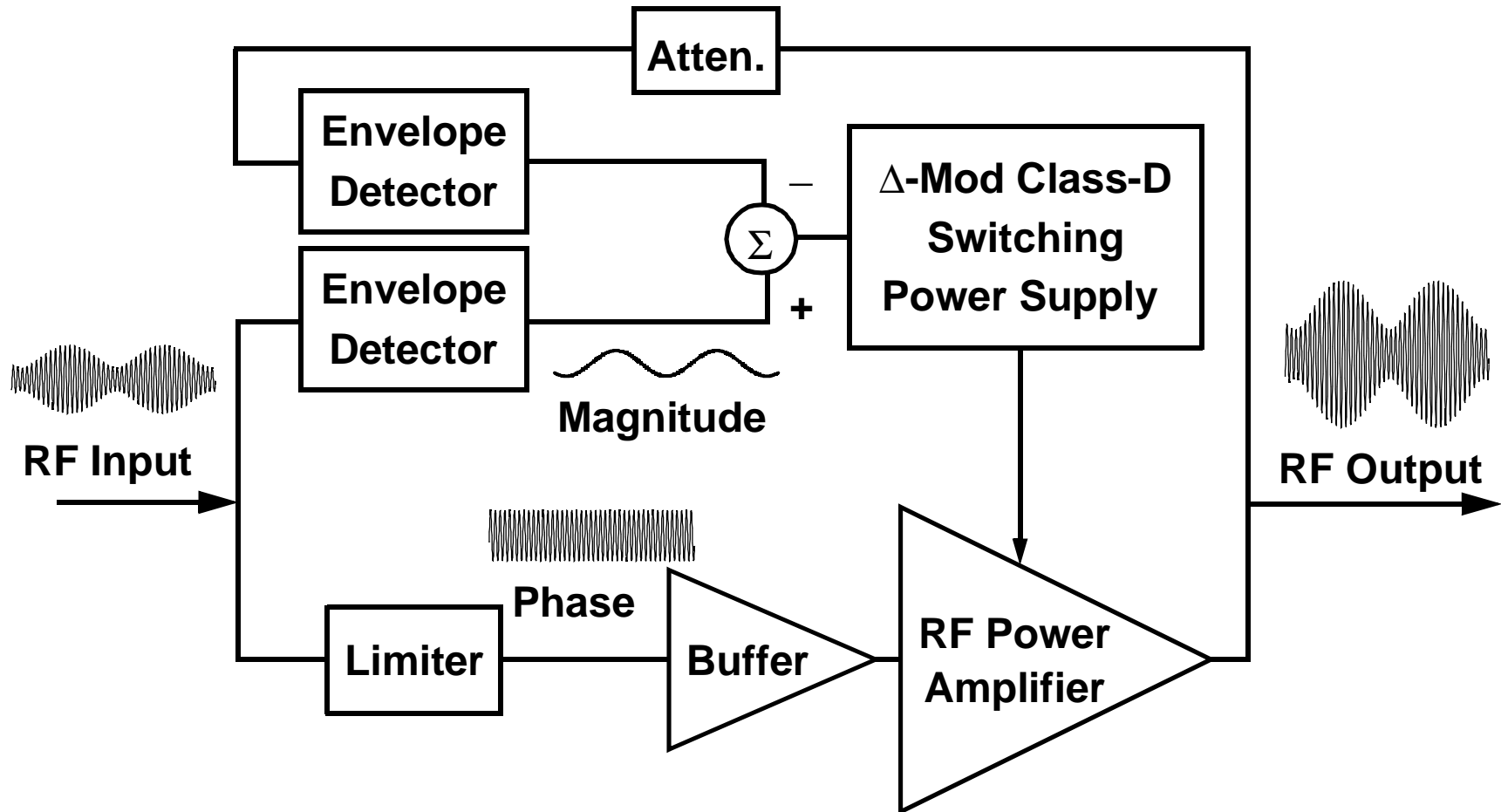
# Envelope Elimination and Restoration



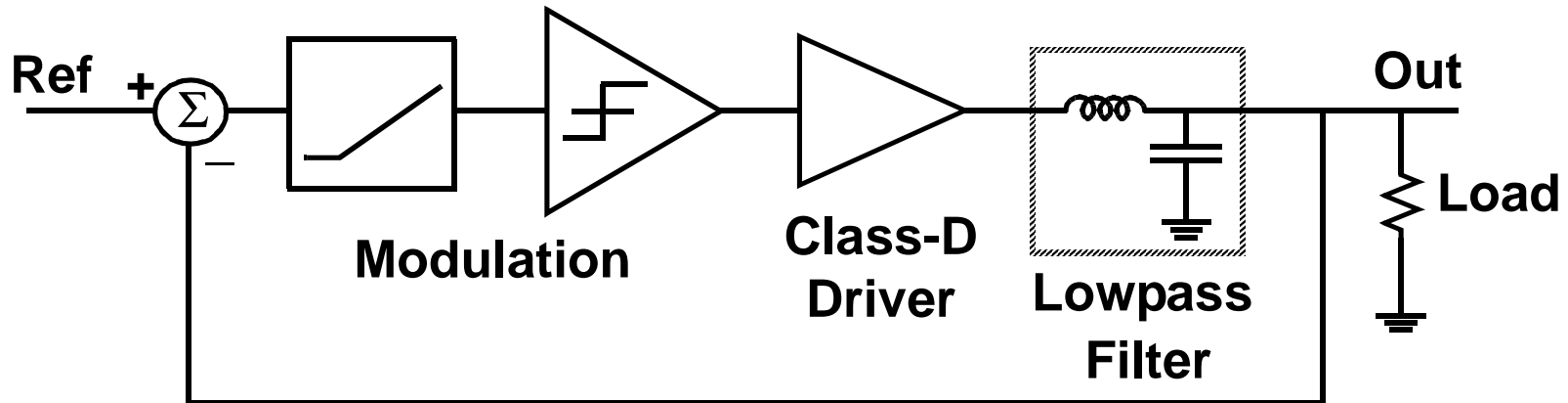
Ref: L. Kahn, Proc IRE, July 1952



# Closed-Loop EER Implementation

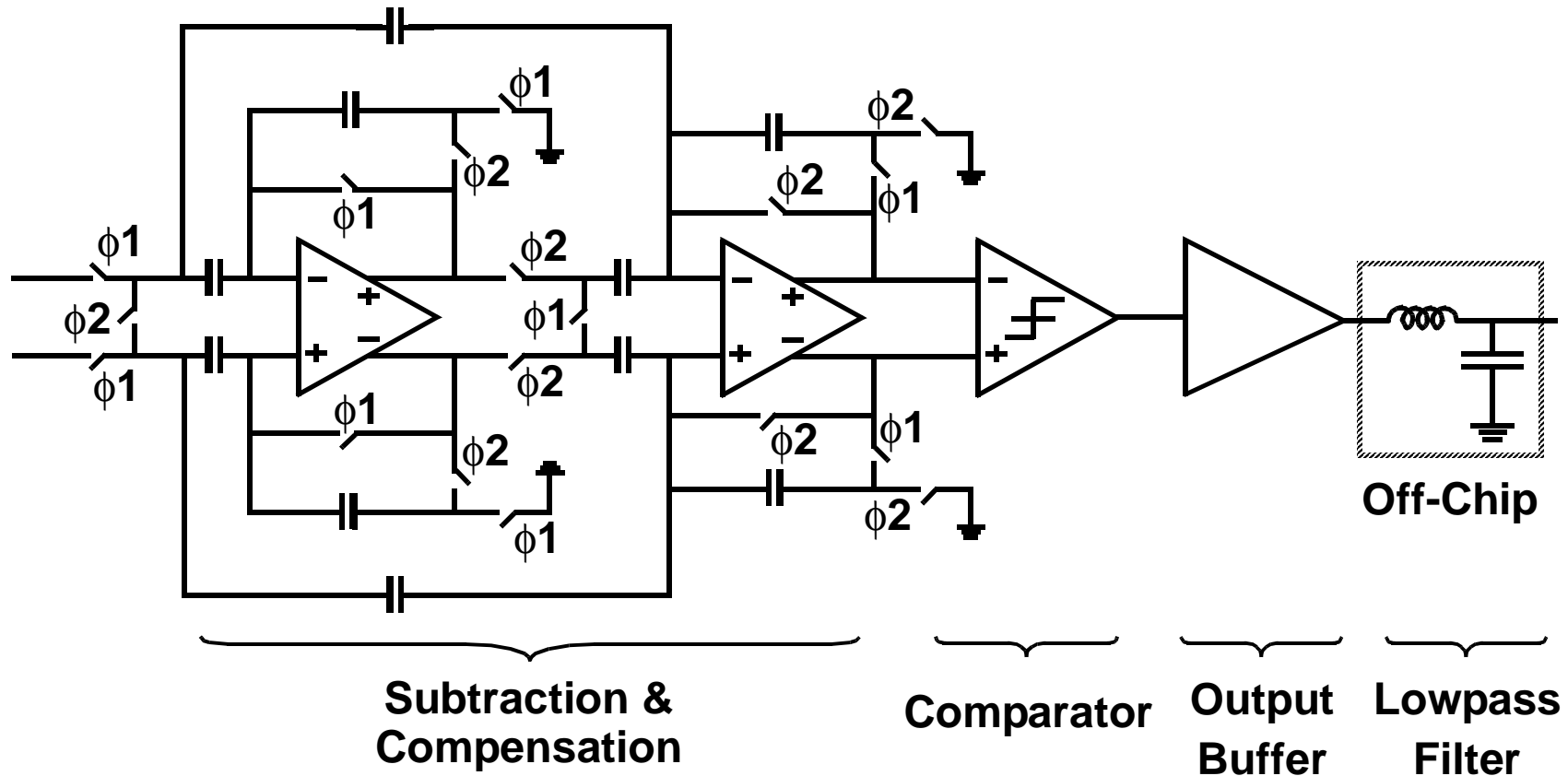


# $\Delta$ -Modulated Switching Power Supply



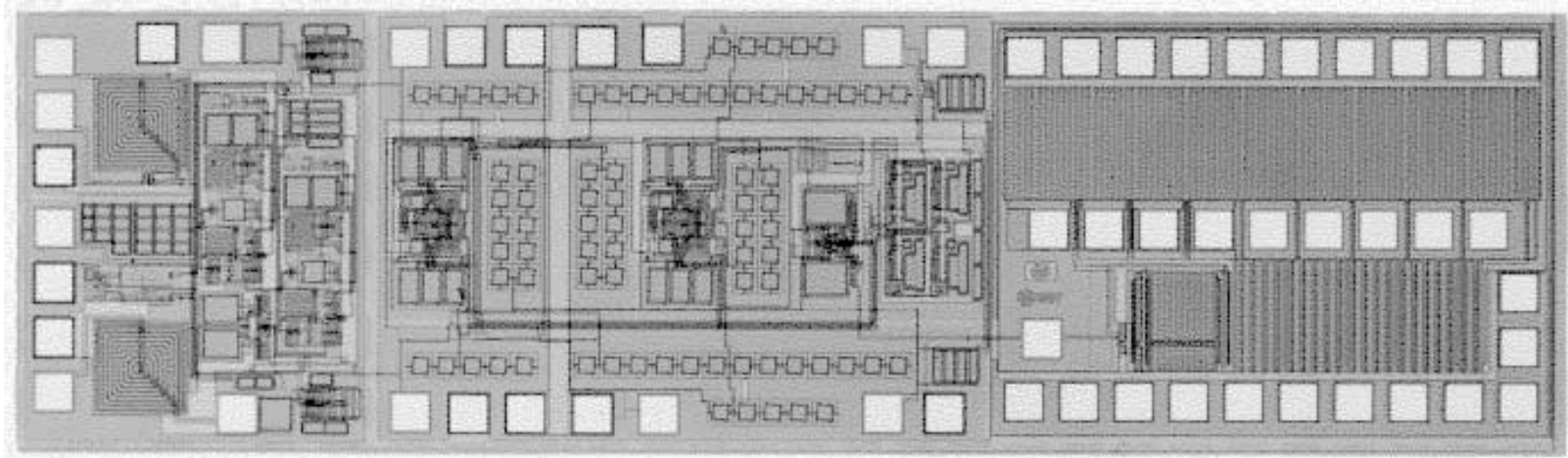
- **Closed-loop system**
- **Modulation to generate a two-level output**  
⇒ Pulse width modulation vs. Delta modulation
- **Efficient Class-D driver**

# Switched-cap Circuit for $\Delta$ Modulation



# Die Photograph

Envelope  
Detector  
(0.03 mm<sup>2</sup>)

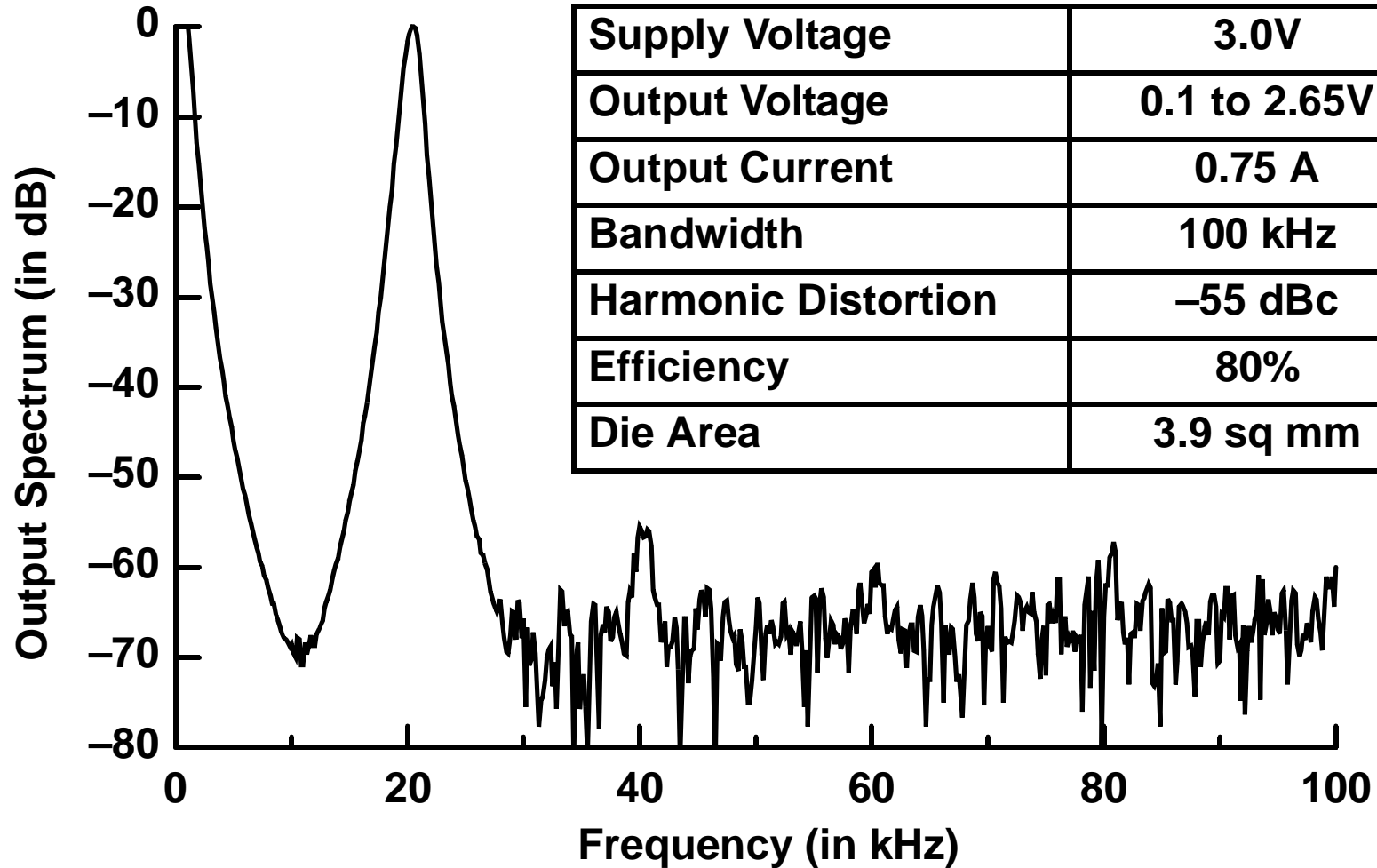


↔  
**Limiter**  
(0.34 mm<sup>2</sup>)

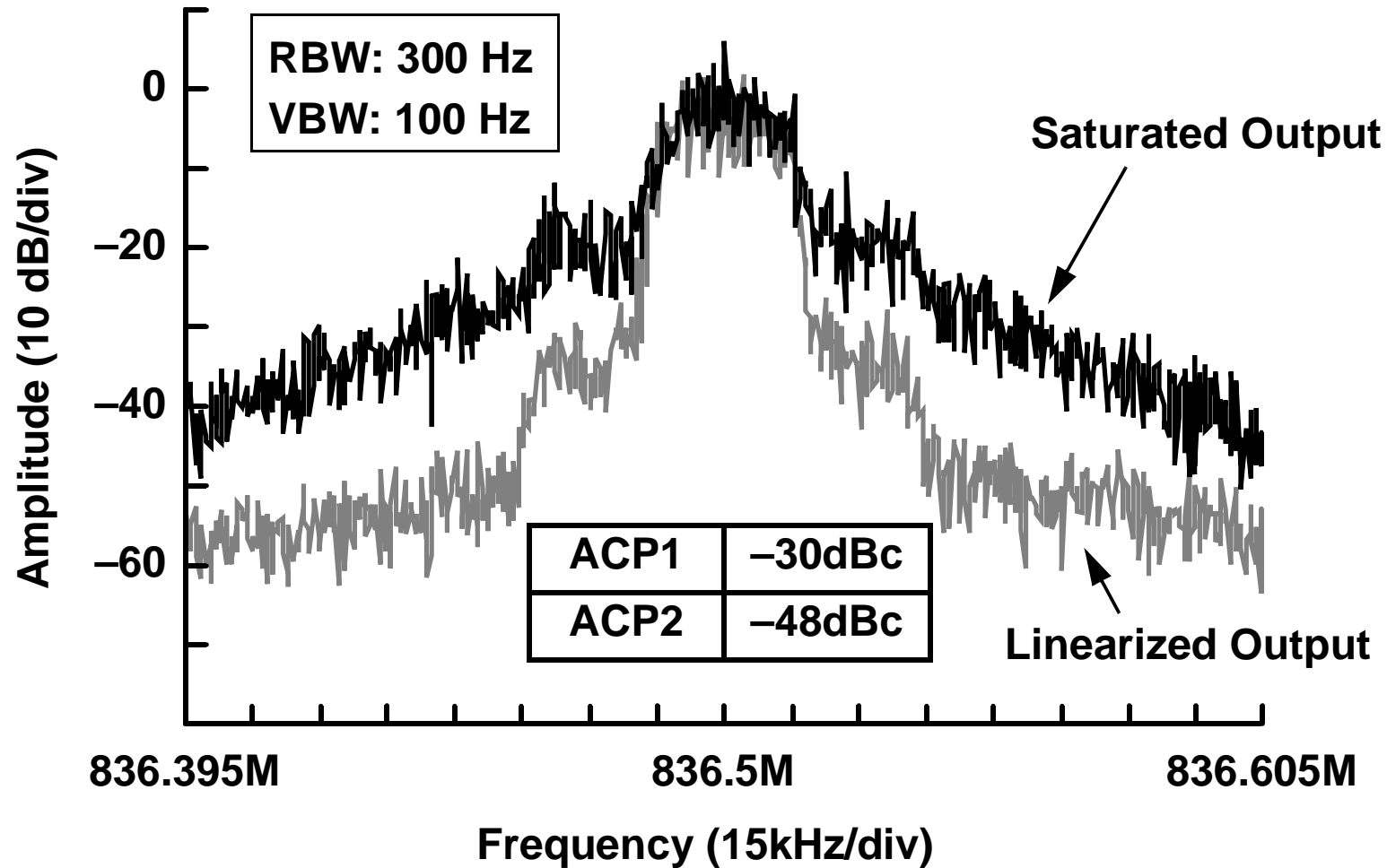
↔  
**Δ-Mod Switching  
Power Supply**  
(2 mm<sup>2</sup>)

↔  
**Buffer**  
(1.9 mm<sup>2</sup>)

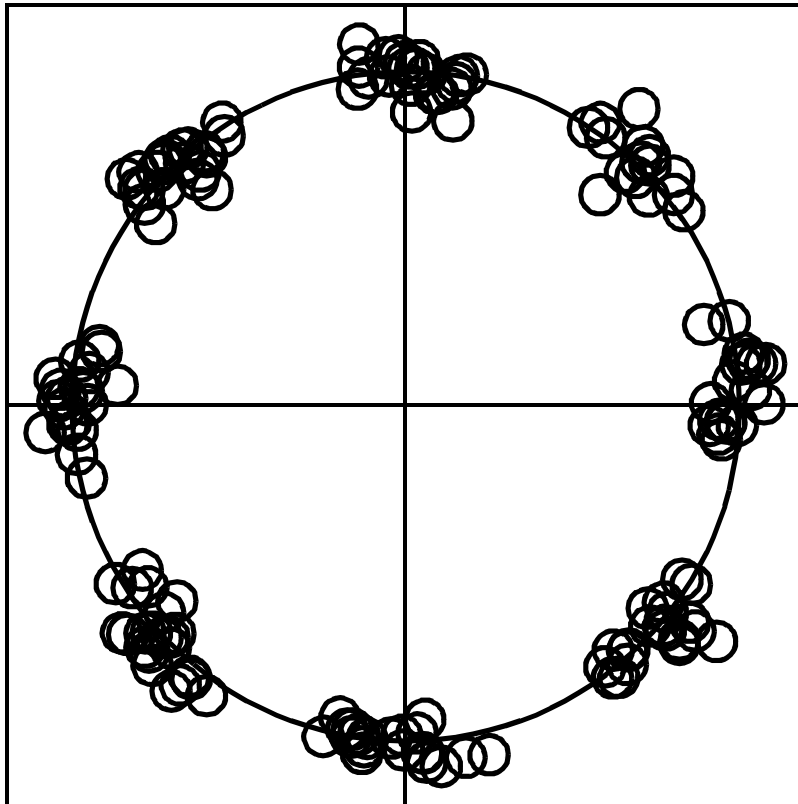
# Switching Power Supply



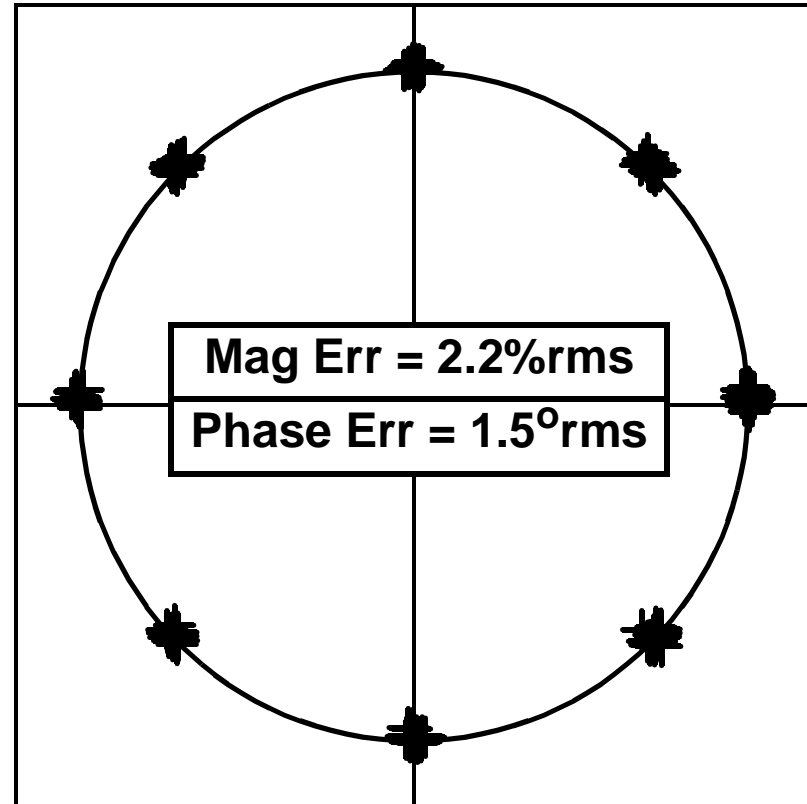
# Spectral Mask of CMOS PA



# $\pi/4$ QPSK Constellation of CMOS PA

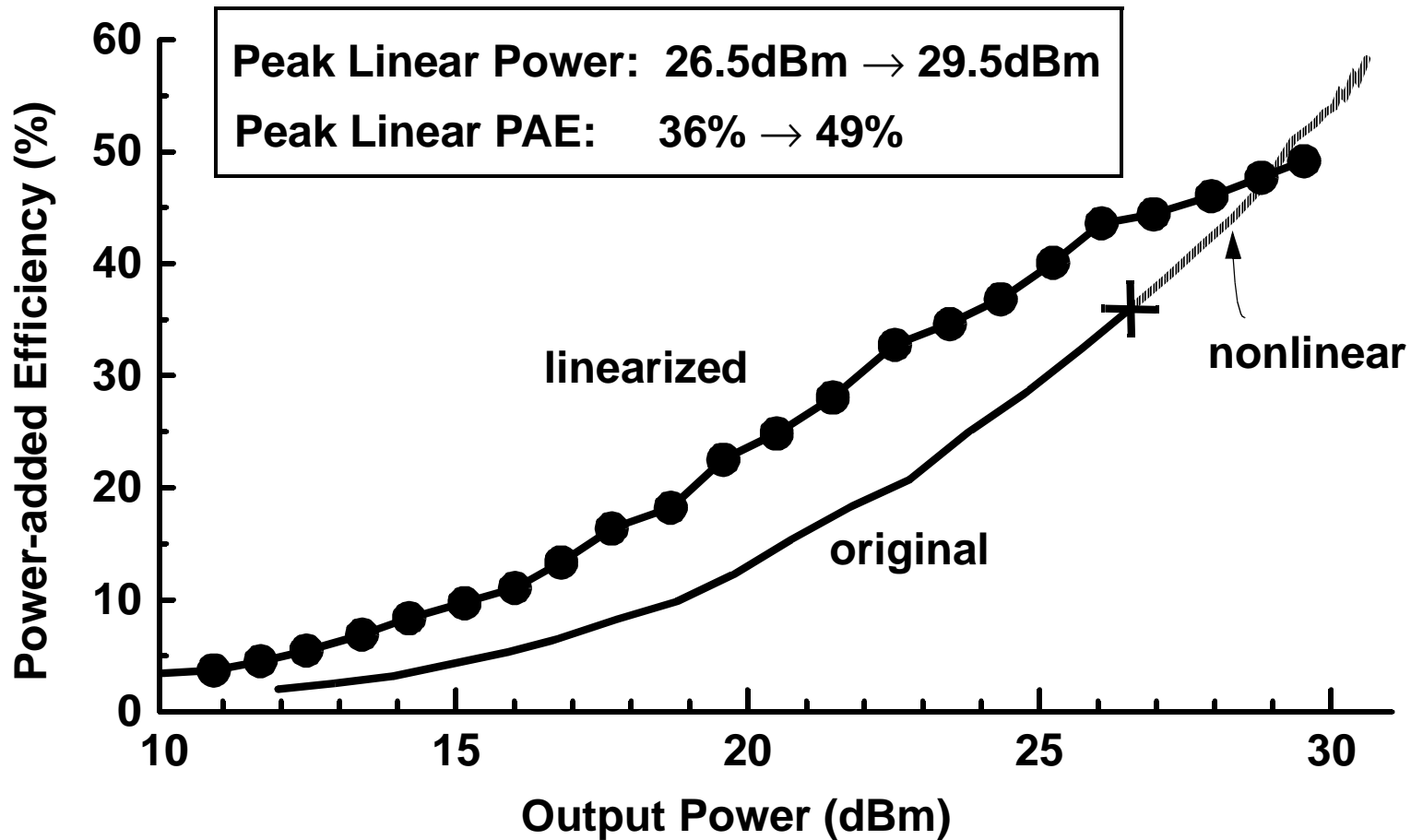


Without Linearization



With Linearization

# Efficiency of 4.8-V GaAs PA





# Conclusion

- **Nonlinear (switched-mode) PA provides**  
**(+) large output power and high efficiency**  
**(-) poor linearity**
- **Linear PA provides**  
**(+) linearity, spectral efficiency**  
**(-) poor efficiency**
- **Linearization using envelope elimination and restoration**  
**(+) linear RF output + high efficiency**  
**(-) implementation complexity**